Dual Channel 1A, Synchronous Step-Down Regulator

General Description

EML3022 is designed with high efficiency step down DC/DC converter and supports dual channel for portable devices applications. It features with extreme low quiescent current with no load which is the best fit for extending battery life during the standby mode.

The device operates from 2.5V to 5.5V input voltage and up to 1A output current capability. High 1.5MHz internal frequency makes small surface mount inductors and capacitors possible and reduces overall PCB board space. Further, build-in synchronous switch makes external Schottky diode is no longer needed and efficiency is improved. EML3022 is designed base on Pulse Width Modulation (PWM) for low output voltage ripple and fixed frequency noise, while Pulse Frequency Modulation (PFM) is used to improve light load efficiency, and Low Dropout (LDO) Mode provides 100% duty cycle operation. Low reference voltage is designed for achieving regulated output down to 0.6V.

The device is available in an adjustable version in E-SOP-8L package.

Features

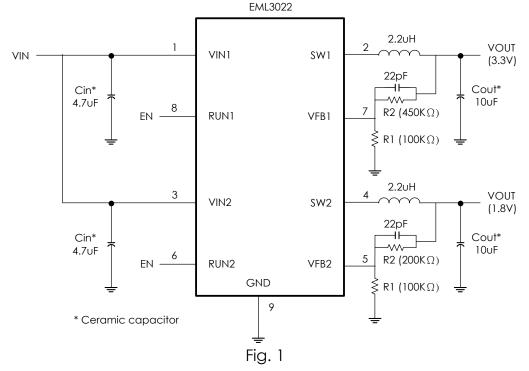
- Achieve 97% efficiency
- Input Voltage : 2.5V to 5.5V
- Output Current up to 1A
- Reference voltage 0.6V
- Quiescent Current 30µ A with No Load
- Internal switching frequency 1.5MHz
- No Schottky Diode needed
- Low Dropout Operation: 100% Duty Cycle
- Shutdown current < 1µ A
- Excellent Line and Load Transient Response
- Over-temperature Protection

Applications

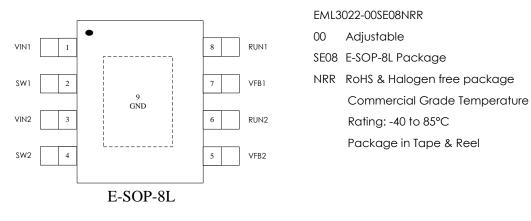
- Blue-Tooth devices
- Cellular and Smart Phones
- Personal multi-media Player (PMP)
- Wireless networking
- Digital Still Cameras
- Portable applications



Typical Application



Package Configuration



Order, Mark & Packing information

Package	Vout(V)	Product ID	Marking	Packing		
E-SOP-8L	adjustable	EML3022-00SE08NRR	ESMT EML3022 Tracking code	Tape & Reel 3K units		



Pin Functions

Pin Name	E-SOP-8L	Function
VIN1	1	Power Input Pin. Must be closely decoupled to GND pin with a $4.7\mu\text{F}$ or
VINT	I	greater ceramic capacitor.
SW1	2	Switch Pin. Must be connected to Inductor. This pin connects to the
3001	2	drains of the internal main and synchronous power MOSFET switches.
VIN2	3	Power Input Pin. Must be closely decoupled to GND pin with a $4.7\mu\text{F}$ or
VINZ	5	greater ceramic capacitor.
SW2	4	Switch Pin. Must be connected to Inductor. This pin connects to the
3₩2	4	drains of the internal main and synchronous power MOSFET switches.
VFB2		Feedback Pin. Receives the feedback voltage from an external resistive
(Adjustable)	5	divider across the output.
VOUT2	5	Output Voltage Pin. An internal resistive divider divides the output
(Fixed voltage)		voltage down for comparison to the internal reference voltage.
RUN2	,	Enable Pin. Minimum 1.2V to enable the device. Maximum 0.4V to shut
KUNZ	6	down the device.
VFB1		Feedback Pin. Receives the feedback voltage from an external resistive
(Adjustable)	7	divider across the output.
VOUT1	7	Output Voltage Pin. An internal resistive divider divides the output
(Fixed voltage)		voltage down for comparison to the internal reference voltage.
RUN1	8	Enable Pin. Minimum 1.2V to enable the device. Maximum 0.4V to shut
KUNI	ö	down the device.
GND	9	Connect to GND.
(Exposed pad)	7	



Absolute Maximum Ratings

Devices are subjected to fail if they stay above absolute maximum ratings.

Input Voltage	-0.3V to 6V
EN, V _{FB} Voltages	– 0.3V to V_{IN}
SW Voltage 0.3V to	o (V _{IN} + 0.3V)
Lead Temperature (Soldering, 10 sec)	260°C

 Operating Temperature Range
 --40°C to 85°C

 Junction Temperature (Notes 1, 3)

 Storage Temperature Range

 ESD Susceptibility HBM
 2KV

 MM
 200V

Thermal data

Package	Thermal resistance	Parameter	Value	
E-SOP-8L	θ _{JA} (Note 4)	Junction-ambient	42°C/W	
	θ _{JC} (Note 5)	Junction-case	10°C/W	

Electrical Characteristics

The \bigcirc denotes specifications which apply over the full operating temperature range, otherwise specifications are T_A = 25°C. V_{IN} = 3.6V unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Units
VIN	Input Voltage Range			2.5		5.5	V
I _{VFB}	Feedback Current					±100	nA
VFB	Regulated Feedback Voltage			0.588	0.600	0.612	V
Vout %	Output Voltage Accuracy	I _{OUT} =100mA	•	-3		+3	%
ΔV_{FB}	Reference Voltage Line Regulation	V _{IN} = 3.0V to 5.5V	•			0.6	%/V
ΔV_{OUT}	Output Voltage Line Regulation	$V_{IN} = 3.0V$ to 5.5V	•			0.6	%/V
Ірк	Peak Inductor Current	$V_{FB} = 0.5V \text{ or } V_{OUT} = 90\%,$		1.5	2.3		А
	PWM Quiescent Current (Note 2)	V_{FB} = 0.5V or V_{OUT} = 90%, dual channel			376		μA
ls	PFM Quiescent Current	$V_{FB} = 0.65V$ or $V_{OUT} = 108\%$, dual channel			30		μA
	Shutdown	V_{RUN} = 0V, V_{IN} = 4.2V, dual channel			0.1	1	μA
£	Oscillator Frequency	V _{FB} = 0.6V or V _{OUT} = 100%	•	1.2	1.5	1.8	MHz
fosc	Short-Circuit Oscillator Frequency	$V_{FB} = 0V \text{ or } V_{OUT} = 0V$	•		900		kHz
Rpfet	R ds(on) of PMOS	I _{sw} = 100mA			0.24		Ω
RNFET	R ds(on) of NMOS	$I_{SW} = -100 \text{mA}$			0.21		Ω
V _{UVLO}	Under Voltage Lock Out				1.8		V
Ilsw	SW Leakage	$V_{RUN} = 0V$, $V_{SW} = 0V$ or $5V$, $V_{IN} = 5V$				±1	μA
	Enable Threshold		•			1.2	V
Vrun	Shutdown Threshold		•	0.4			V
Irun	RUN Leakage Current		•			±1	μA

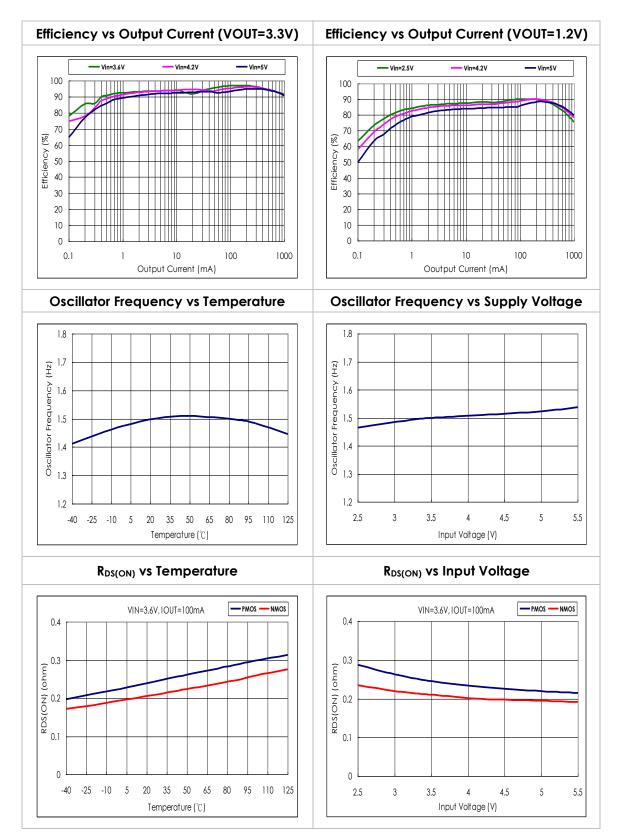
Note 1: T_J is a function of the ambient temperature T_A and power dissipation P_D ($T_J = T_A + (P_D)(165^{\circ}C/W)$) **Note 2:** Dynamic quiescent current is higher due to the gate charge being delivered at the switching frequency. **Note 3:** This IC is build-in over-temperature protection to avoid damage from overload conditions.

Note 5: $\hat{\theta}_{JC}$ represents the resistance to the heat flows the chip to package top case.

Note 4: θ _{JA} is measured in the natural convection at TA=25°C on a high effective thermal conductivity test board (4 layers , 2S2P) of JEDEC 51-5 thermal measurement standard.

Typical Performance Characteristics

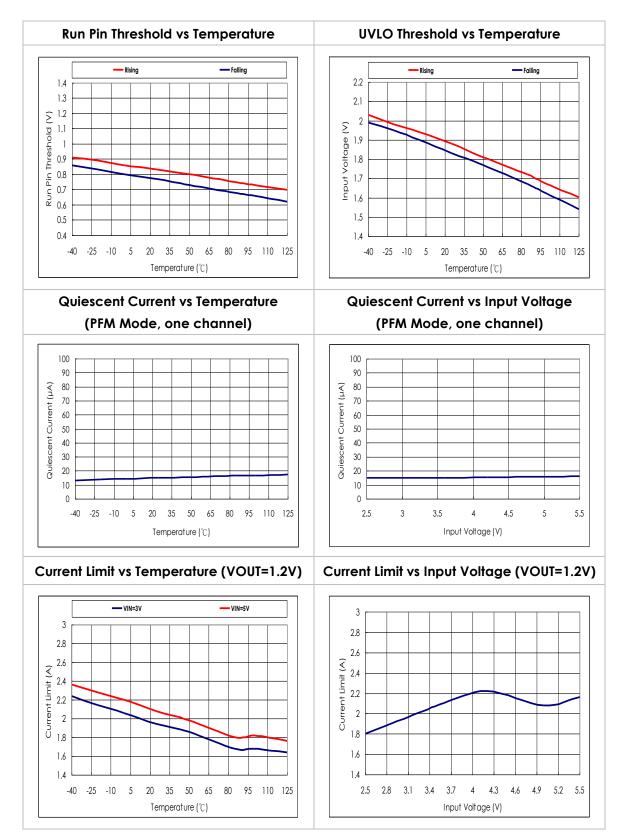
VIN=3.6V, TA=25°C, unless otherwise specified





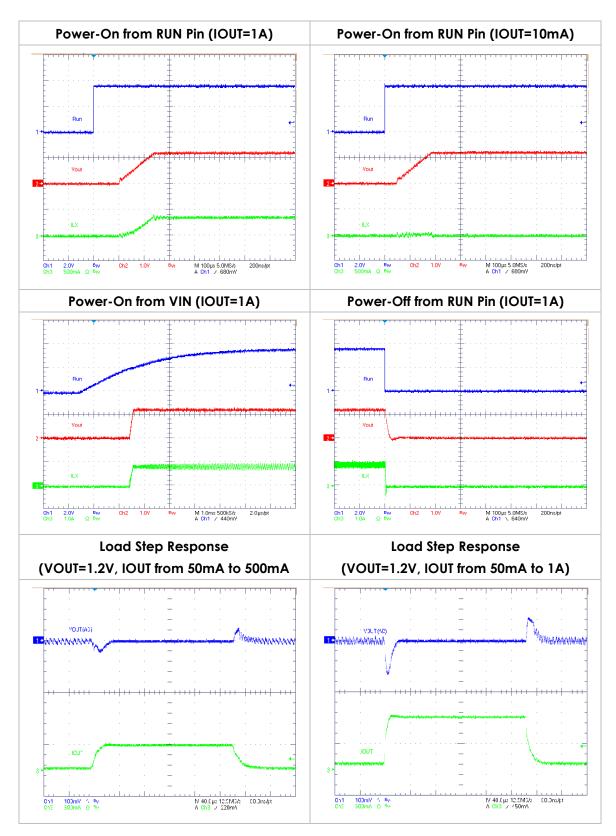
Typical Performance Characteristics (cont.)

VIN=3.6V, TA=25°C, unless otherwise specified



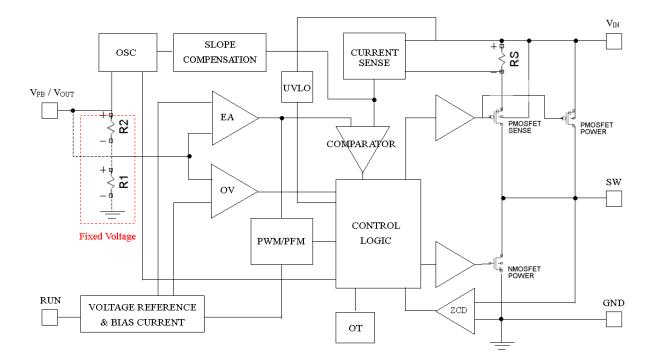
Typical Performance Characteristics (cont.)

VIN=3.6V, TA=25°C, unless otherwise specified





Functional Block Diagram

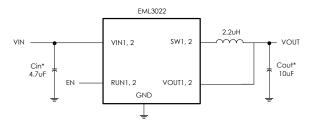




Applications

The typical application circuit of adjustable version is shown in Fig.1.

Fixed voltage version is shown below:



Inductor Selection

Basically, inductor ripple current and core saturation are two factors considered to decide the Inductor value. A low DCR inductor is preferred.

$C_{\mbox{\scriptsize IN}}$ and $C_{\mbox{\scriptsize OUT}}$ Selection

A low ESR input capacitor can prevent large voltage transients at V_{IN} . The RMS current of input capacitor is required larger than I_{RMS} calculated by:

$$I_{\text{RMS}} \cong I_{\text{OMAX}} \ \frac{\sqrt{V_{\text{OUT}} \left(V_{\text{IN}} - V_{\text{OUT}}\right)}}{V_{\text{IN}}} \qquad \text{Eq. 1}$$

ESR is an important parameter to select $C_{\mbox{\scriptsize OUT}}.$ The output ripple $V_{\mbox{\scriptsize OUT}}$ is determined by:

$$\Delta V_{OUT} \cong \Delta I_{L} \left(ESR + \frac{1}{8 \cdot f \cdot C_{OUT}} \right) \qquad \text{Eq. 2}$$

Higher values, lower cost ceramic capacitors are now available in smaller sizes. These ceramic capacitors have high ripple currents, high voltage ratings and low ESR that make them ideal for switching regulator applications. Optimize very low output ripple and small circuit size is doable from Cout selection since Cout does not affect the internal control loop stability. It is recommended to use the X5R or X7R which have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Output Voltage (EML3022 adjustable)

In the adjustable version, the output voltage can be determined by:

$$V_{OUT} = 0.6 V \left(1 + \frac{R_2}{R_1} \right)$$
 Eq. 3

Thermal Considerations

Although thermal shutdown is build-in in EML3022 that protect the device from thermal damage, the total power dissipation that EML3022 can sustain should be base on the package thermal capability. The formula to ensure the safe operation is shown in Note 1.

To avoid the EML3022 from exceeding the maximum junction temperature, the user will need to do some thermal analysis.

Guidelines for PCB Layout

To ensure proper operation of the EML3022, please note the following PCB layout guidelines:

1. The GND trace, the SW1, 2 trace and the VIN1, 2 trace should be kept short, direct and wide.

2. VFB1, 2 pin must be connected directly to the feedback resistors. Resistive divider R1/R1 must be connected and parallel to the output capacitor Cout.

3. The Input capacitor C_{IN} must be connected to pin VIN1, 2 as closely as possible.

4. Keep SW1, 2 nodes away from the sensitive VFB1, 2 nodes since this node is with high frequency and voltage swing.

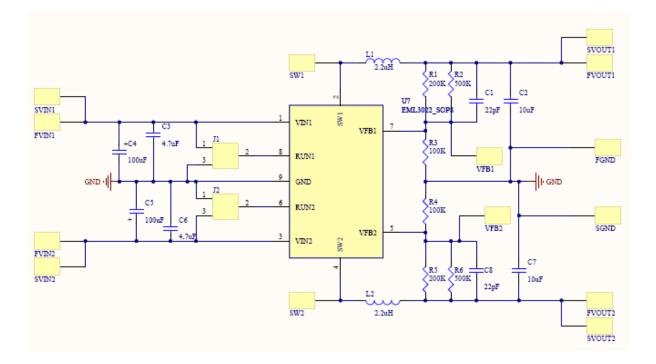
5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.





Applications

Typical schematic for PCB layout

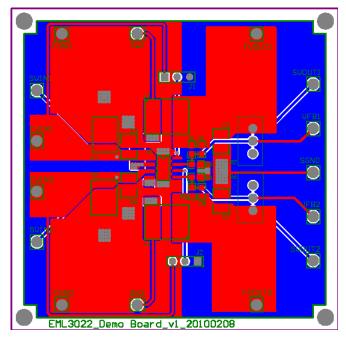


Note.

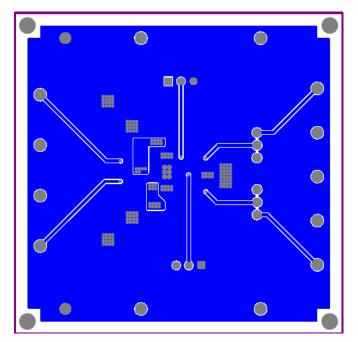
R2, R6 and C4, C5 are preserved passive component locations for testing purpose. Please remove it during normal application.



Typical schematic for PCB layout (cont.)



Top Layer

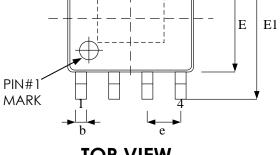


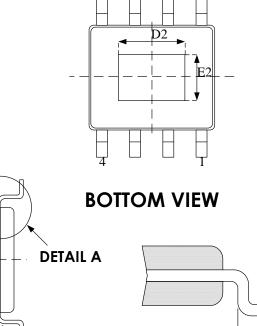
Bottom Layer





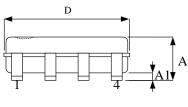
Package Outline Drawing SOP-8 (E) (150 mil)





DETAIL A

TOP VIEW



SIDE VIEW

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Symph ol	Dimension in mm			
Symbol	Min	Max		
А	-	1.70		
A1	0.00	0.15		
b	0.31	0.51		
С	0.10	0.25		
D	4.80	5.00		
Е	3.81	4.00		
E1	5.79	6.20		
е	1.27	BSC		
L	0.40	1.27		

Exposed pad					
	Dimension in mm				
	Min	Max			
D2	2.80	3.50			
E2	2.00	2.60			



Old order, Mark & Packing information

Package	Vout(V)	Product ID	Marking	Packing
E-SOP-8L	adjustable	EML3022-00SE08NRR	EMP EML3022 Tracking code	Tape & Reel 3K units

Revision History

Revision	Date	Description
0.1	2010.04.29	Original
0.2	2010.09.16	 Updated "Output Voltage Line Regulation" maximum is 0.6% Updated "Reference Voltage Line Regulation" Maximum is 0.6%
0.3	2010.09.21	1)Skip "Preliminary" 2)Update package information
1.0	2012.08.23	Modify package outline drawing
1.1	2013.11.04	Marking logo change to ESMT POD format change
1.2	2021.07.14	Modify E-SOP-8 Dimension



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